



**Product data sheet** 

## 1. General description

Dual ultrafast power diodes in a TO220 plastic package.

### 2. Features and benefits

- Low forward voltage drop
- Low leakage current
- Soft reverse recovery characteristics
- High thermal cycling performance

## 3. Applications

- Home appliance power supply
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

## 4. Quick reference data

able 1. Q	uick reference data					
Symbol	Parameter	Conditions	Values		Unit	
Absolute	maximum rating					
V <sub>R</sub>	repetitive peak reverse voltage	DC	600		V	
I <sub>O(AV)</sub>	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 124 °C; square-wave pulse; both diodes conducting	20		A	
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 140 °C; square-wave pulse; per diode	20		A	
I <sub>FSM</sub> non-repetitive peak forward current		$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	120			A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	132			A
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics	·				
V <sub>F</sub>	forward voltage	$I_{F}$ = 10 A; $T_{j}$ = 25 °C; per diode; <u>Fig. 6</u>	-	1.3	1.7	V
		$I_F = 10 \text{ A}; T_j = 150 \text{ °C}; \text{ per diode}; Fig. 6$	-	1.0	1.35	V
Dynamic	characteristics	·				
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	30	50	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	40	55	ns
		$I_F = 0.5 \text{ A}; I_r = 0.25 \text{ A}; I_R = 1 \text{ A};$ $T_i = 25 \text{ °C}; \text{ per diode}$	-	-	35	ns

### Table 1. Quick reference data

# **5. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	К	cathode		
3	A2	anode 2		K
mb	К	mounting base; connected to cathode		sym125

# 6. Ordering information

Table 3. Ordering information								
Type number	Package	Orderable part number	Packing	Small packing	Package	Package		
	Name		method	quantity	version	issue date		
BYV410-600P	TO220	BYV410-600PQ	Tube	50	TO220E	26-April-2019		

# 7. Marking

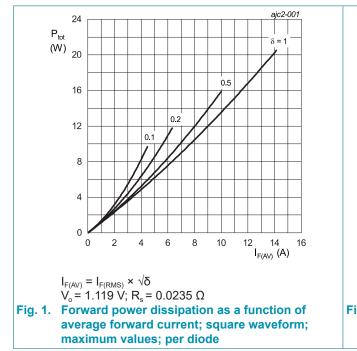
Table 4. Marking codes							
Type number	Marking codes						
BYV410-600P	BYV410-600P						

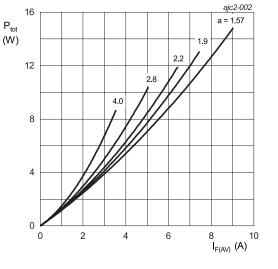
## 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage		600	V
$V_{\text{RWM}}$	crest working reverse voltage		600	V
V <sub>R</sub>	reverse voltage	DC	600	V
I <sub>O(AV)</sub>	average forward current	δ = 0.5; T <sub>mb</sub> ≤ 124 °C; square-wave pulse; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	20	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 140 °C; square-wave pulse; per diode	20	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	120	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	132	A
T <sub>stg</sub>	storage temperature		-55 to 175	°C
T <sub>j</sub>	junction temperature		175	°C

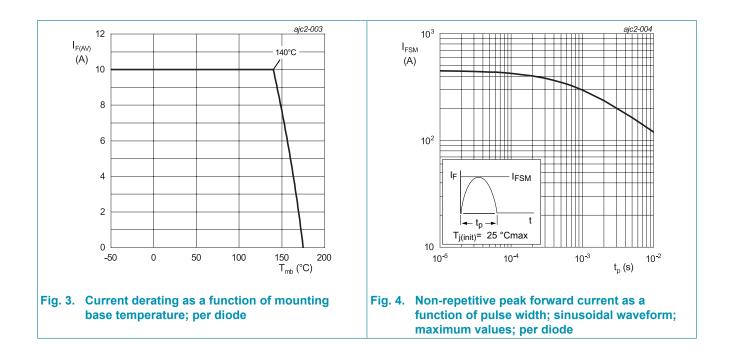




 a = form factor = I<sub>F(RMS)</sub> / I<sub>F(AV)</sub> V<sub>o</sub> = 1.119 V; R<sub>s</sub> = 0.0235 Ω
Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

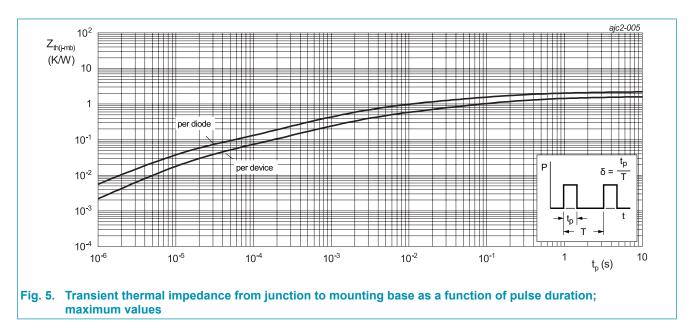
Dual ultrafast power diode

**BYV410-600P** 



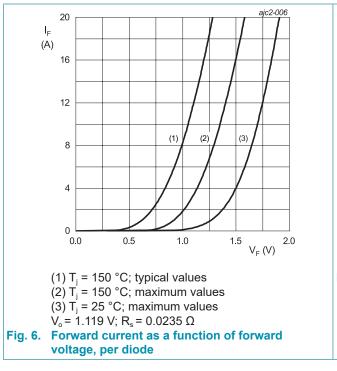
## 9. Thermal characteristics

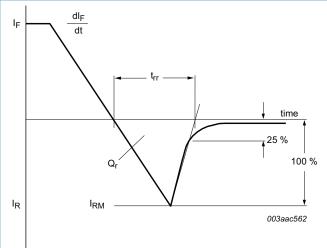
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5	-	-	2.2	K/W
	mounting base	with heatsink compound; both diodes conducting; Fig. 5	-	-	1.6	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



## **10. Characteristics**

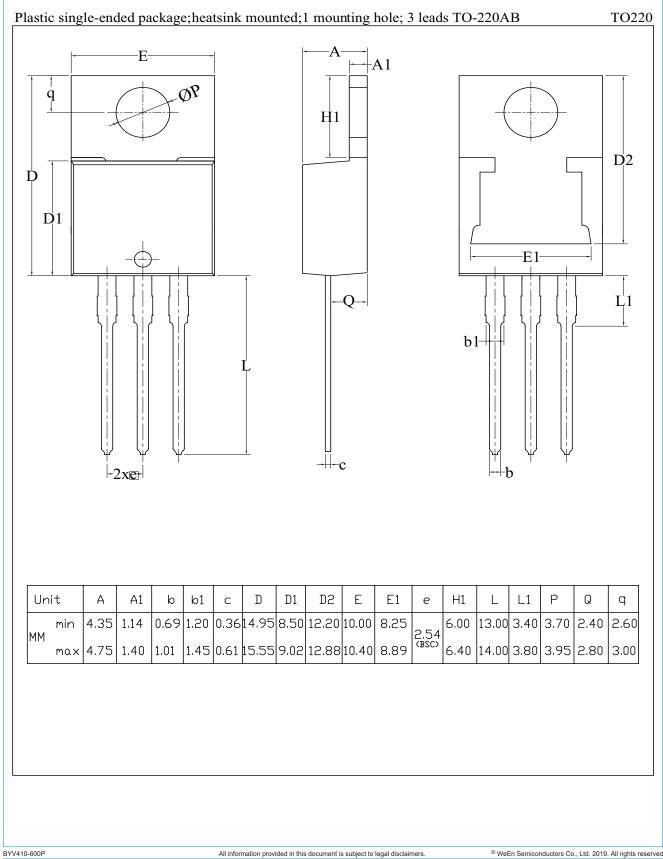
Table 7. Cl	haracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.3	1.7	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.0	1.35	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	1	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	0.1	0.5	mA
Dynamic	characteristics					
Q <sub>r</sub>	recovered charge	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 7</u>	-	22	-	nC
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 7</u>	-	30	50	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	40	55	ns
		$I_F = 0.5 \text{ A}; I_r = 0.25 \text{ A}; I_R = 1 \text{ A};$ $T_j = 25 \text{ °C}; \text{ per diode}$	-	-	35	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	1.6	-	A
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$	-	1.1	-	A
E <sub>as</sub>	non-repetitive avalanche energy	I <sub>R</sub> = 4.8 A; T <sub>j(init)</sub> = 25 °C; L = 15 mH	130	175	-	mJ





### Fig. 7. Reverse recovery definitions; ramp recovery

# 11. Package outline



### **BYV410-600P**

### Dual ultrafast power diode

# 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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